



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Product Summary

BV_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX $T_A = +25^\circ C$
-30V	$1\Omega @ V_{GS} = -4.5V$	-0.6A
	$1.5\Omega @ V_{GS} = -2.5V$	-0.5A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

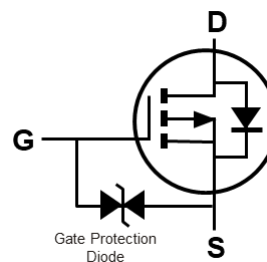
- DC-DC converters
- Load switches
- Power-management functions

Mechanical Data

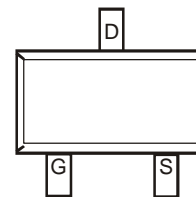
- Package: SOT323
- Package Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Alloy 42 Leadframe.
Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)



Top View



Equivalent Circuit


 Pin-Out
Top View

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	T _A = +25°C	I _D	-0.6	A
		T _A = +70°C		-0.5	
Maximum Body Diode Forward Current (Note 6)			I _S	-0.48	A
Pulsed Drain Current (10μs Pulse, Duty Cycle=1%)			I _{DM}	-1.9	A

Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	0.44	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	287	°C/W
Total Power Dissipation (Note 6)			P _D	0.57	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	220	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	—	-1.1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.7	1	Ω	V _{GS} = -4.5V, I _D = -400mA
			0.8	1.5		V _{GS} = -2.5V, I _D = -200mA
			1.0	2		V _{GS} = -1.8V, I _D = -100mA
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0V, I _S = -300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	54	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	10.9	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	5.8	—	pF	
Total Gate Charge	Q _g	—	1.0	—	nC	V _{GS} = -4.5V, V _{DS} = -15V, I _D = -1A
Total Gate Charge	Q _g	—	1.6	—	nC	V _{GS} = -8V, V _{DS} = -15V I _D = -1A
Gate-Source Charge	Q _{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.1	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.8	—	ns	V _{DD} = -10V, R _L = 10Ω V _{GS} = -4.5V, R _G = 6Ω
Turn-On Rise Time	t _R	—	11	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	45	—	ns	
Turn-Off Fall Time	t _F	—	20	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

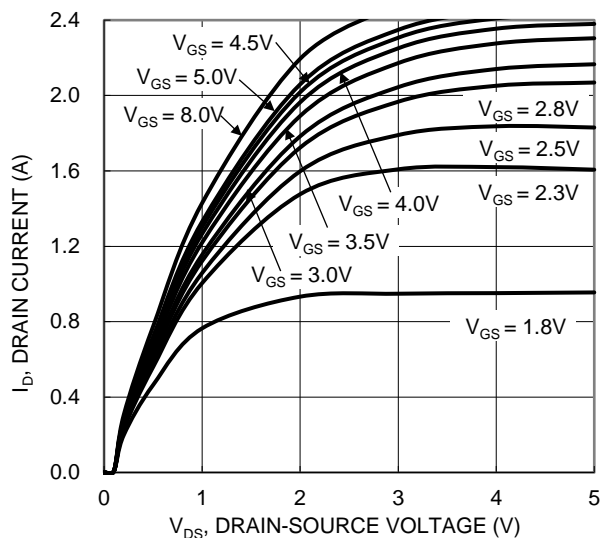


Figure 1. Typical Output Characteristic

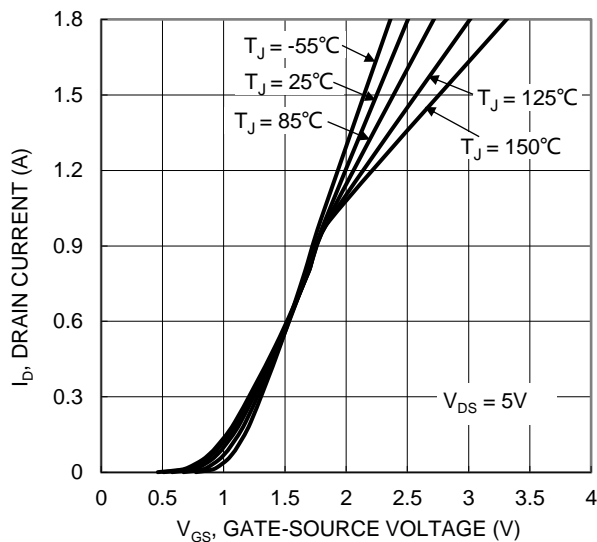


Figure 2. Typical Transfer Characteristic

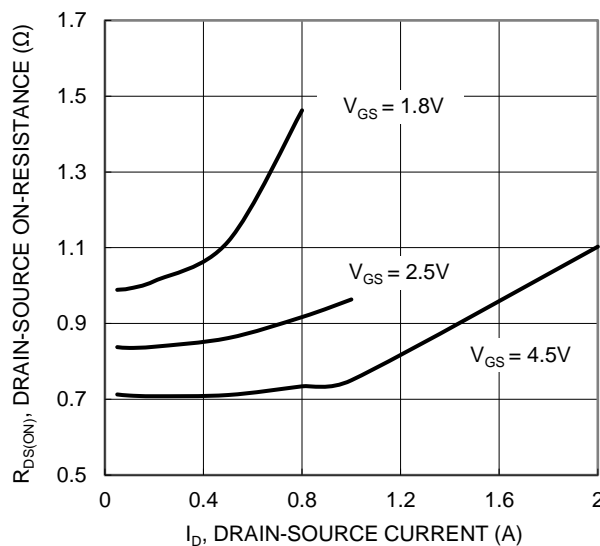


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

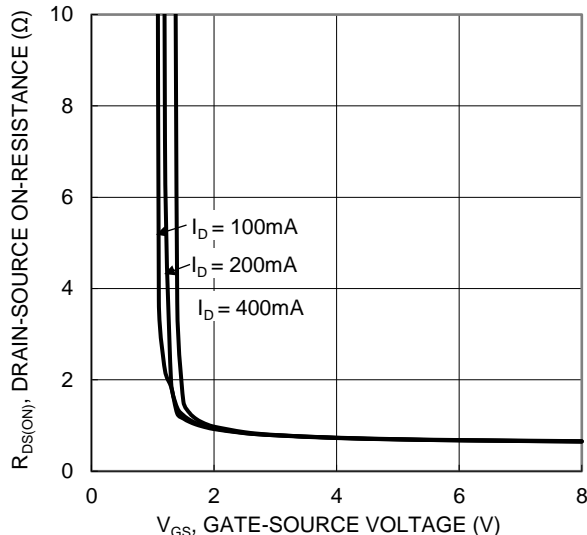


Figure 4. Typical Transfer Characteristic

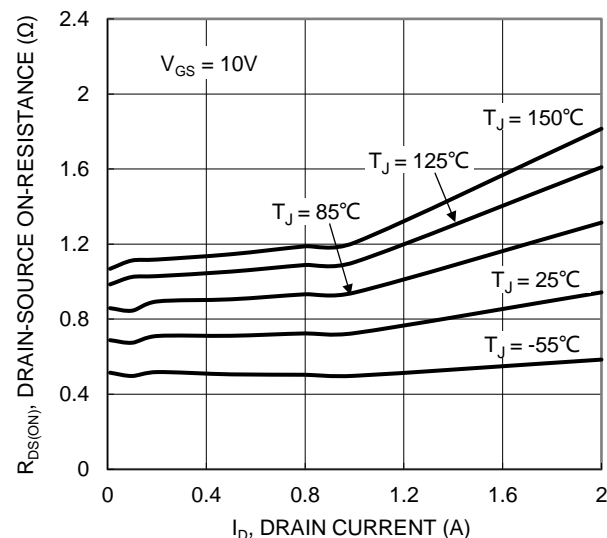


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

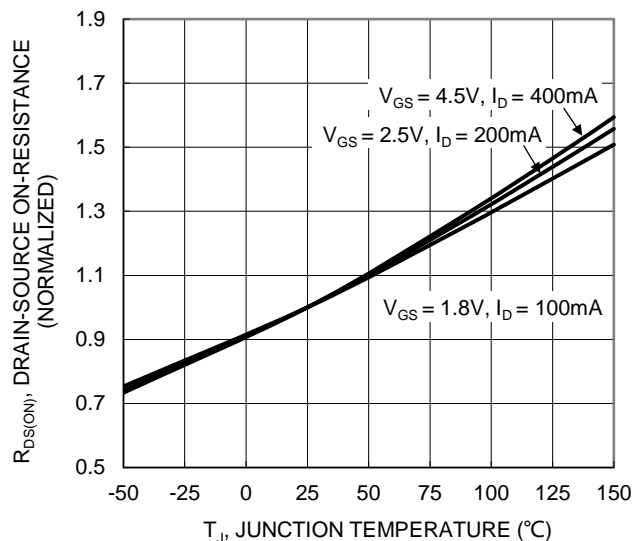


Figure 6. On-Resistance Variation with Temperature

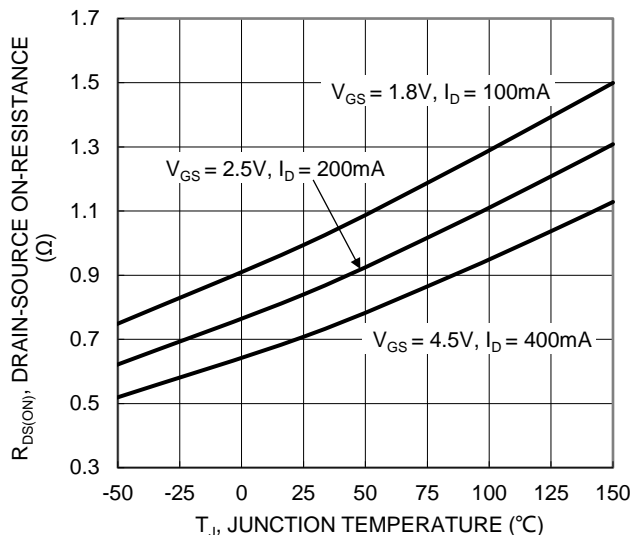


Figure 7. On-Resistance Variation with Temperature

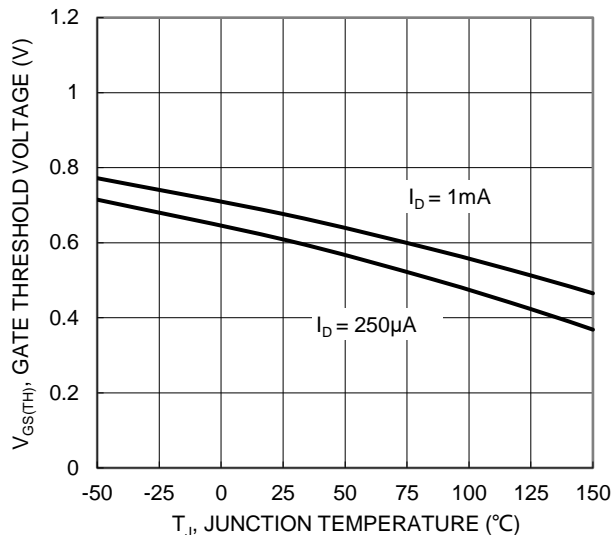


Figure 8. Gate Threshold Variation vs. Junction Temperature

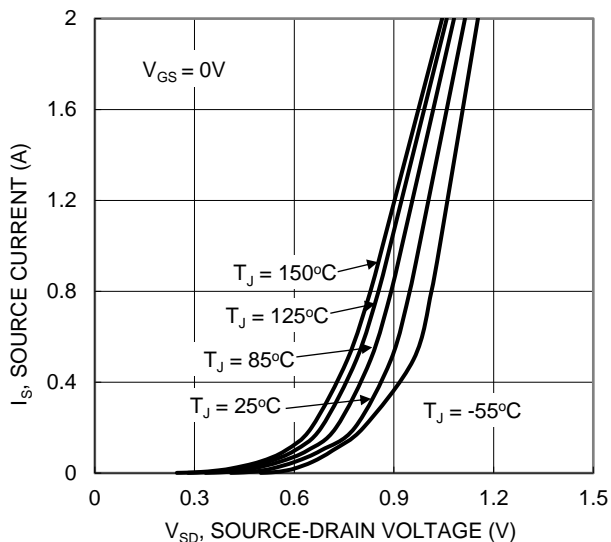


Figure 9. Diode Forward Voltage vs. Current

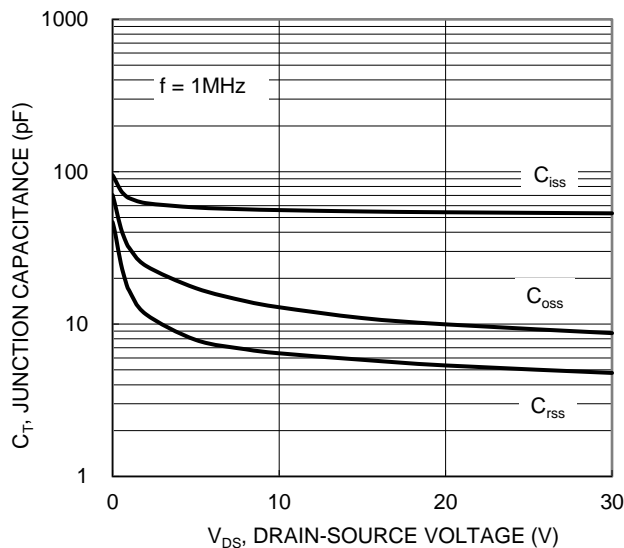


Figure 10. Typical Junction Capacitance

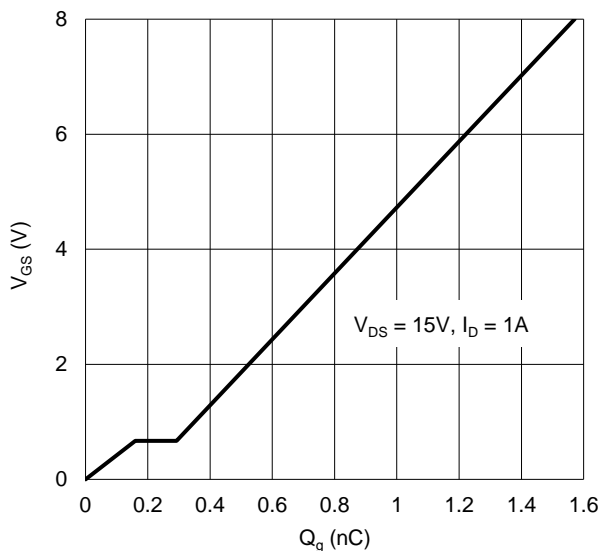


Figure 11. Gate Charge

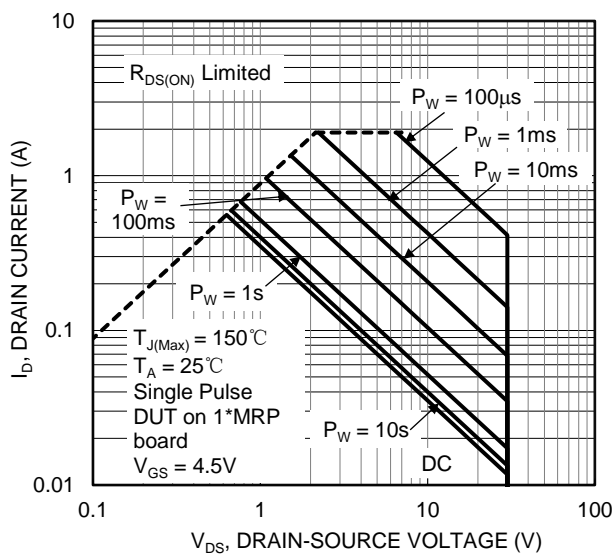


Figure 12. SOA, Safe Operation Area

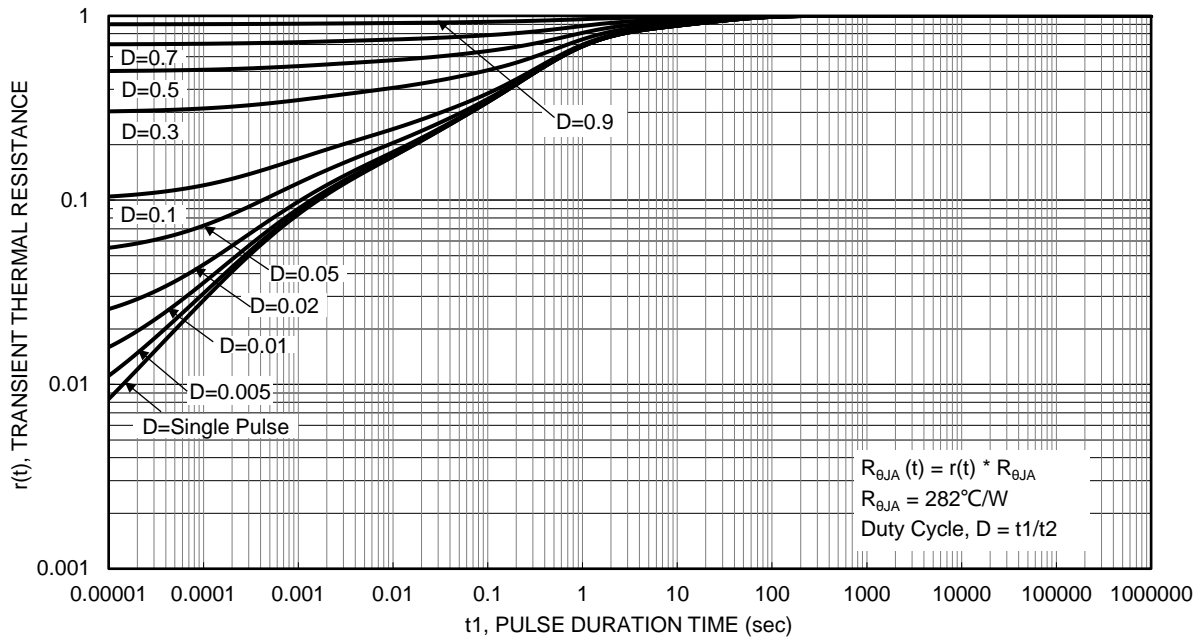
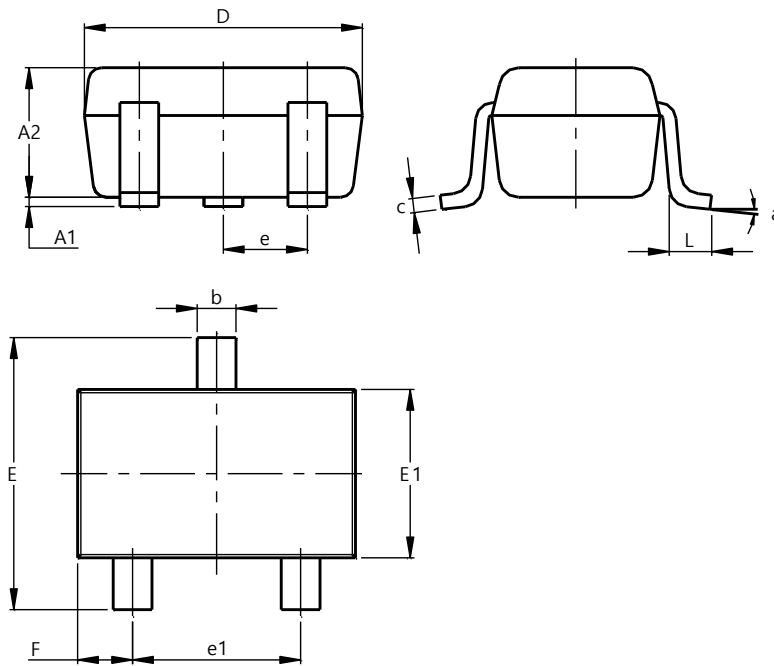


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

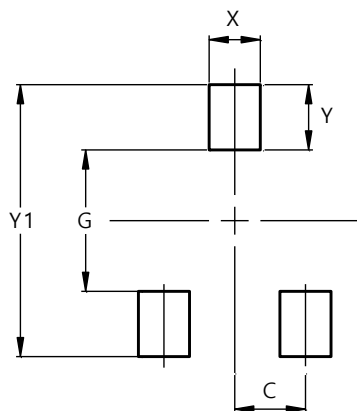
SOT323



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500